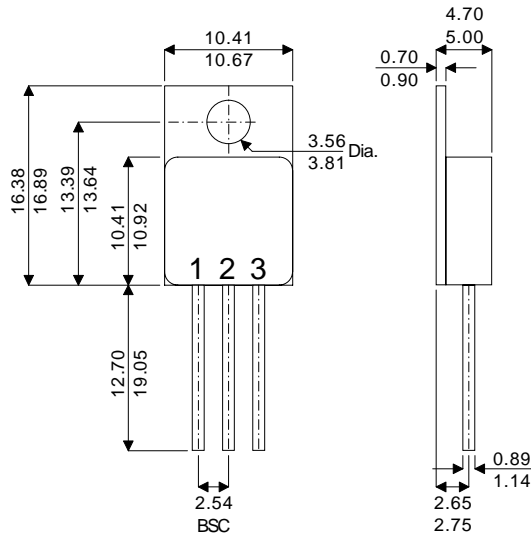


MECHANICAL DATA

Dimensions in mm (inches)



TO-220M – Metal Package

Pad 1 – Gate Pad 2 – Drain Pad 3 – Source

**P-CHANNEL
POWER MOSFET
FOR HI-REL
APPLICATIONS**

V_{DSS} **-100V**
 $I_{D(cont)}$ **-13A**
 $R_{DS(on)}$ **0.21Ω**

FEATURES

- HERMETICALLY SEALED TO-220 METAL PACKAGE
- SIMPLE DRIVE REQUIREMENTS
- LIGHTWEIGHT
- SCREENING OPTIONS AVAILABLE
- ALL LEADS ISOLATED FROM CASE

ABSOLUTE MAXIMUM RATINGS ($T_{case} = 25^{\circ}C$ unless otherwise stated)

V_{GS}	Gate – Source Voltage	±20V
I_D	Continuous Drain Current @ $T_{case} = 25^{\circ}C$	-13A
I_D	Continuous Drain Current @ $T_{case} = 100^{\circ}C$	-8.2A
I_{DM}	Pulsed Drain Current	-52A
P_D	Power Dissipation @ $T_{case} = 25^{\circ}C$	60W
	Linear Derating Factor	0.48W/°C
T_J, T_{stg}	Operating and Storage Temperature Range	-55 to 150°C
$R_{\theta JC}$	Thermal Resistance Junction to Case	2.1°C/W max.
$R_{\theta JA}$	Thermal Resistance Junction to Ambient	80°C/W max.

ELECTRICAL CHARACTERISTICS ($T_C = 25^\circ\text{C}$ unless otherwise stated)

Parameter	Test Conditions	Min.	Typ.	Max.	Unit	
STATIC ELECTRICAL RATINGS						
BV_{DSS}	Drain – Source Breakdown Voltage	$V_{GS} = 0$	$I_D = 1\text{mA}$	-100	V	
$\frac{\Delta BV_{DSS}}{\Delta T_J}$	Temperature Coefficient of Breakdown Voltage	Reference to 25°C $I_D = 1\text{mA}$		-0.09	$\text{V}/^\circ\text{C}$	
$R_{DS(on)}$	Static Drain – Source On–State Resistance	$V_{GS} = 10\text{V}$	$I_D = -8.2\text{A}$		0.21	
		$V_{GS} = 10\text{V}$	$I_D = -13\text{A}$		0.24	
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}$	$I_D = 250\mu\text{A}$	-2	-4	V
g_{fs}	Forward Transconductance	$V_{DS} \geq 15\text{V}$	$I_{DS} = -8.2\text{A}$	6.2		$\text{S}(\bar{v})$
I_{DSS}	Zero Gate Voltage Drain Current	$V_{GS} = 0$	$V_{DS} = 0.8BV_{DSS}$		25	μA
			$T_J = 125^\circ\text{C}$			250
I_{GSS}	Forward Gate – Source Leakage	$V_{GS} = 20\text{V}$			100	nA
I_{GSS}	Reverse Gate – Source Leakage	$V_{GS} = -20\text{V}$			-100	
DYNAMIC CHARACTERISTICS						
C_{iss}	Input Capacitance	$V_{GS} = 0$			1400	pF
C_{oss}	Output Capacitance	$V_{DS} = 25\text{V}$			600	
C_{rss}	Reverse Transfer Capacitance	$f = 1\text{MHz}$			200	
Q_g	Total Gate Charge	$V_{GS} = 10\text{V}$	$I_D = -13\text{A}$	31	60	nC
		$V_{DS} = 0.5BV_{DSS}$				
Q_{gs}	Gate – Source Charge	$I_D = -13\text{A}$		3.7	13	nC
Q_{gd}	Gate – Drain (“Miller”) Charge	$V_{DS} = 0.5BV_{DSS}$		7	35.2	
$t_{d(on)}$	Turn–On Delay Time	$V_{DD} = -50\text{V}$ $I_D = -13\text{A}$ $R_G = 9.1\Omega$			35	ns
t_r	Rise Time				85	
$t_{d(off)}$	Turn–Off Delay Time				85	
t_f	Fall Time				65	
SOURCE – DRAIN DIODE CHARACTERISTICS						
I_S	Continuous Source Current				-13	A
I_{SM}	Pulse Source Current				-52	
V_{SD}	Diode Forward Voltage	$I_S = -13\text{A}$	$T_J = 25^\circ\text{C}$		-4.2	V
		$V_{GS} = 0$				
t_{rr}	Reverse Recovery Time	$I_S = -13\text{A}$	$T_J = 25^\circ\text{C}$		280	ns
Q_{rr}	Reverse Recovery Charge	$d_i / d_t \leq 100\text{A}/\mu\text{s}$			3.6	μC
		$V_{DD} \leq 50\text{V}$				
PACKAGE CHARACTERISTICS						
L_D	Internal Drain Inductance	(from 6mm down drain lead pad to centre of die)			8.7	nH
L_S	Internal Source Inductance	(from 6mm down source lead to centre of source bond pad)			8.7	